MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

LMV358IDR-MS/LMV358IPWR-MS/LMV358IDGKR-MS

Product specification





GENERAL DESCRIPTION

The LMV358 is dual CMOS operational amplifier that uses the proprietary auto-calibration technique to simultaneously provides very lowoffset voltage, near-zero drift over time and temperature. These miniature, high-precision, low quiescent current amplifiers offer high-impedance inputs that have a common-mode range 200mV beyond the rails, and rai-to-rail output that swings within 50mV of the rails, single or dual supplies as low as 2.1V(±1.35V) and up to 5.5V(±2.75V) can be used. These devices are optimized for low voltage, single supply operation.

The LMV358 offers excellent CMRR without the crossover associated with traditional complementary input stages.T his design results in superior performance for driving analog-to-digital converters(ADC) without degradation of differ ential linearity. The LMV358IDR-MS is available in the 8-pin SOP-8、VSSOP and TSSOP packages.

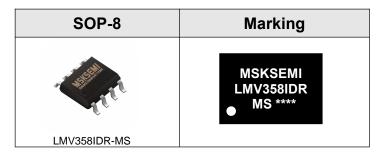
FEATURES

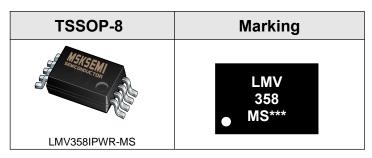
- VDD range:2.1V to 5.5V
- Low Offset Voltage:0.5mV (Typical)
- Low Drift: 0.65μV/C(Typical)
- Low Noise
- Quiescent Current:50μA (Total)
- Rail to Rail Input/Output
- MicroSize Packages:SOP-8、 VSSOP and TSSOP

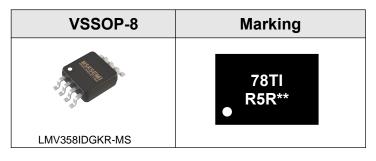
APPLICATIONS

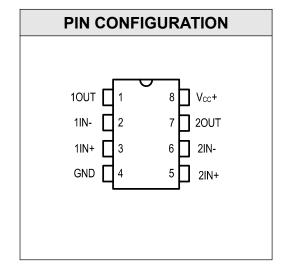
- Transducers
- Temperature Measurement
- Electronic Scales
- Medical instrumentation
- Handheld Test Equipment

Reference News











PIN DESCRIPTION

Pin Name	Pin Number	Description		
10UT	1	Output 1		
1IN-	2	Inverting input 1		
1IN+	3	Noninverting input 1		
GND	4	Negative(lowest)power supply		
2IN+	5	Noninverting input 2		
2IN-	6	Inverting input 2		
2OUT	7	Output 2		
Vcc+	8	Positive(highest)power supply		

SIMPLIFIED SCHEMATIC

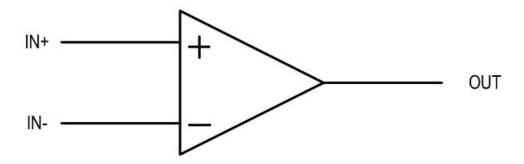


Figure 1.Simplified Schematic

ABSOLUTE MAXIMUM RATINGS

Thermal Resistance θ Jc	130°℃/W
Supply Voltage	2.1to 5.5V
Signal Input Terminals Voltage	0.1 to (V+)+0.1V
Operating Junction Temperature	150°C
Operating Temperature Range	55°C to 125°°C
Storage Temperature	65°C to 150°C



ELECTRICAL CHARACTERISTICS

(AtTa=25 $^{\circ}\text{C}$,RL=10k to Vs/2,and Vour=Vs/2,unless

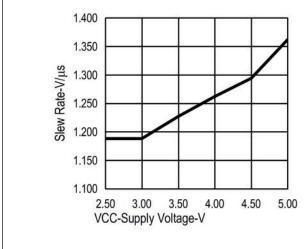
PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
Input Offset Voltage	$Vs=\pm 2.5V$	-2	0. 5	2	mV
nput Offset Voltage Drift	TA=-55℃ to 125℃		0.65		μV/°C
Power Supply Rejection Ratio	Vs =2.1V to 5.5V TA=-55°C to 125°C	80	90		dB
Input Bias Curren	TA=25°C		2		pA
Input Offset Curren			1		pA
Common-mode Voltage Range		(V-)-0.1		(V+)+0.1	V
Common-mode Rejectior Ratio	(V-)-0.1 <vcm<(v+)+0.' TA=-55℃ to 125℃</vcm<(v+)+0.' 	80	95		dB
Open Loop Voltage Gain	(V-)+100mV <vo<(v+)-10 0mv<br="">RL=10k TA=-55°Cto125°C</vo<(v+)-10>	80	100		dB
Gain-bandwidth product	CL=120pF		1. 5		MHz
Slew Rate	G=+1		1. 2		V/μs
Specified Voltage Range		2. 1		5. 5	V
Quiescent Current (Total)	1o=0A		50		μА
Operating Temperature Range		-55		125	$^{\circ}$ C
Storage Temperature Range		-65		150	$^{\circ}$

60



TYPICAL PERFORMANCE CHARACTERISTICS



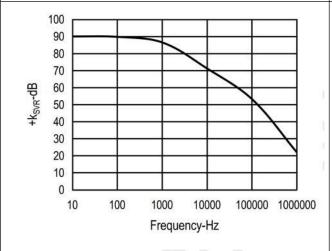


50 40 30 10 10 10 2.0 3.0 4.0 5.0 Supply Voltage-V

85°C

Figure 2. Slew Rate vs Supply Voltage

Figure 3. Supply Current vs Supply Voltage



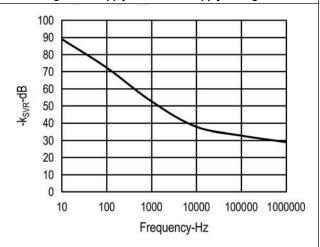
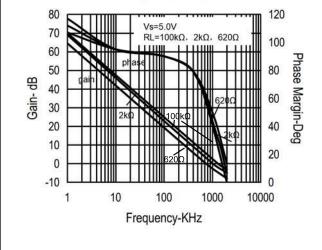


Figure 4. +ksvR vs Frequency

Figure 5. -ksvR vs Frequency



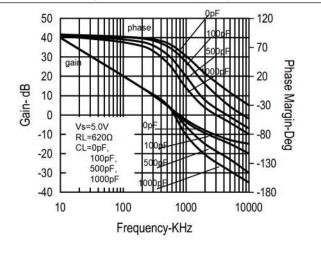
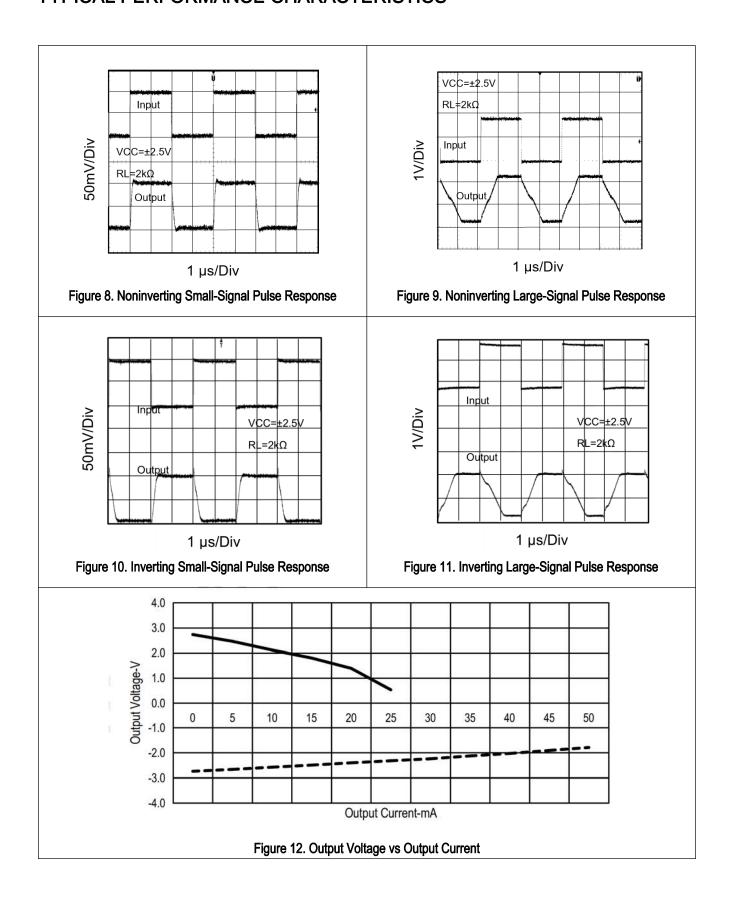


Figure 6. Frequency Response vs Resistive Load

Figure 7. Frequency Response vs Capacitive Load



TYPICAL PERFORMANCE CHARACTERISTICS





FUNCTIONAL DESCRIPTION

Operating Voltage

The LMV358 device is fully specified and ensured for operation from 2.1V to 5.5V.In addition,many specifications apply from -55°C to 125°C. Parameters that vary significantly with operating voltages or temperature are shown in the Typical Characteristics graphs

Unity-Gain Bandwidth

The unity-gain bandwidth is the frequency up to which an amplifier with a unity gain may be operated without greatly distorting the signal. The LMV358 device has a 1.5-MHz unity-gain bandwidth.

Slew Rate

The slew rate is the rate at which an operational amplifier can change its output when there is a change on the input. The LMV358 devices have a $1.2\text{-V/}\mu$ s slew rate. The LMV358 is characterized to perform with this technique; the recommended resistor value is approximately 20 k.

Device Functional Modes

The LMV358 device has a single functional mode. The device is powered on as long as the power supply voltage is between 2.1V(±1.35V)and 5.5V(±2.75V).

APPLICATIONS INFORMATION

The LMV358 is a unity-gain stable, precision operational amplifier with very low offset voltage drift; these devices are also free from output phase reversal. Applications with noisy or high-impedance power supplies require decoupling capacitors close to the device power-supply pins. In most cases, 0.1 µF capacitors are adequate.

Typical Application

Figure 13 shows a simple circuit to convert a single-ended input into differential output. The LMV358 could be used to build this circuit. The circuit is composed of two amplifiers. One amplifier acts as a buffer and creates a voltage, Vour+. The second amplifier inverts the input and adds a reference voltage to generate Vour-. Both Vour+ and Vour-range from 0.5 to 2V. The difference, VDIFF, is the difference between VouT+ and VouT-.

Detailed Design Procedure

Linearity over the input range is key for good dc accuracy. The common mode input range and the output swing limitations determine the linearity. In general, an amplifier with rail-to-rail input and output swing is required. Bandwidth is a key concern for this design. Because LMV358 has a bandwidth of 1 MHz, this circuit will only be able to process signals with frequencies of less than 1 MHz.

Because the transfer function of Vour-is heavily reliant on resistors(R1,R2,R3,and R4),use resistors with low tolerances to maximize performance and minimize error. This design used resistors with resistance values of 36 k with tolerances measured to be within 2%. If the noise of the system is a key parameter, the user can select smaller resistance values (6 k or lower) to keep the overall system noise low. This ensures that the noise from the resistors is lower than the amplifier noise.



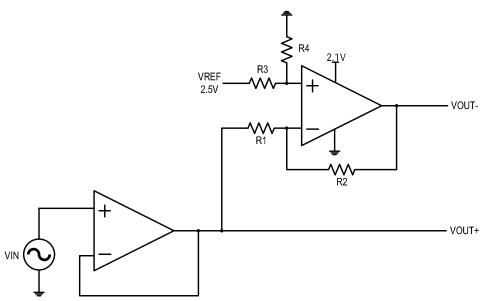
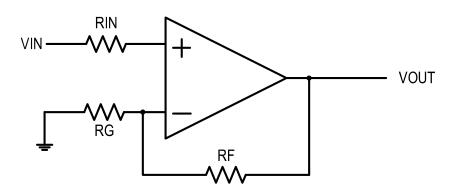


Figure 13. Schematic for Single-Ended Input to Differential Output Conversion

LAYOUT

Use good PCB layout practices for best operational performance of the device, including:

- Keep the length of input traces as short as possible.
- Run the input traces as far away from the supply lines as possible to reduce parasitic coupling.
- Place components close to device and to each other to reduce parasific capacitance and parasitic errors.
- Use low-ESR,ceramic bypass capacitors to reduce the coupled noise by providing low impedance power sources local to the analog circuitry.
- Grounding for analog and digital portions of circuitry separately to suppresse the noise.





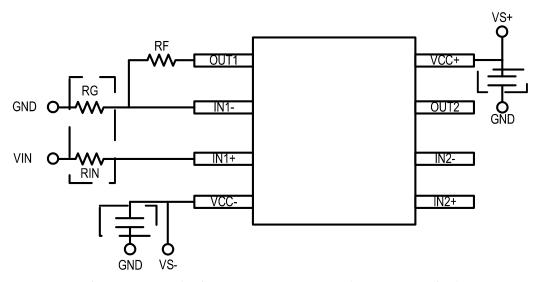
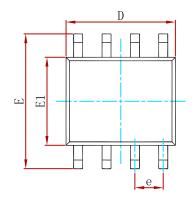
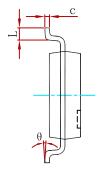


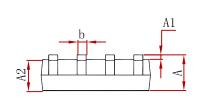
Figure 14. Operational Amplifier Schematic and Board Layout for Noninverting Configuration



PACKAGE MECHANICAL DATA

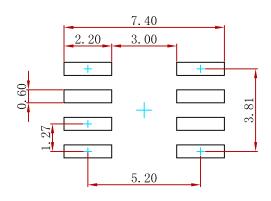






Symbol	Dimensions Ir	Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
A	1.350	1.750	0.053	0.069	
A1	0. 100	0. 250	0.004	0.010	
A2	1. 350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
c	0. 170	0. 250	0.007	0.010	
D	4.800	5. 000	0. 189	0.197	
e	1. 270	1. 270 (BSC)		0.050 (BSC)	
E	5. 800	6. 200	0. 228	0.244	
E1	3.800	4.000	0. 150	0. 157	
L	0.400	1. 270	0.016	0.050	
θ	0°	8°	0°	8°	

Suggested Pad Layout



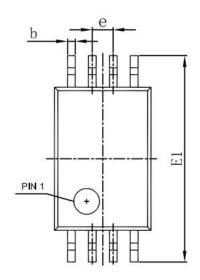
- 1.Controlling dimension:in millimeters. 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

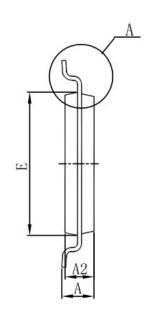
REEL SPECIFICATION

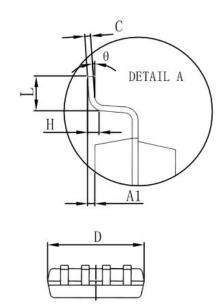
P/N	PKG	QTY
LMV358IDR-MS	SOP-8	2500PCS



TSSOP-8 Package Outline Dimensions







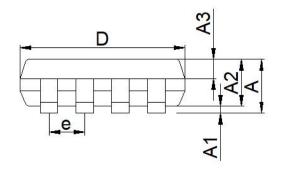
Symbol	Dimensions Ir	n Millimeters	Dimensions In Inches		
Symbol	Min	Iin Max		Max	
D	2.900	3.100	0.114	0.122	
Е	4.300	4.500	0.169	0.177	
b	0.190	0.300	0.007	0.012	
c	0.090	0.200	0.004	0.008	
E1	6.250	6.550	0.246	0.258	
A		1.200		0.047	
A2	0.800	1.000	0.031	0.039	
A1	0.050	0.150	0.002	0.006	
e	0.65 (BSC)		0.026 (BSC)		
L	0.500	0.700	0.020	0.028	
Н	0 .25(T YP)		0 .01(T YP)		
9	1.	7。	1.	7。	

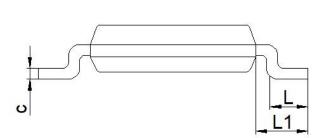
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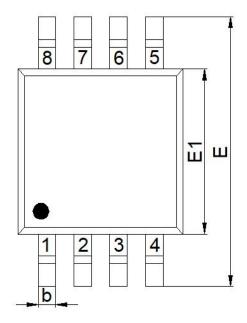
P/N	PKG	QTY
LMV358IPWR-MS	TSSOP-8	2500



VSSOP8 封装外形尺寸







VSSOP8 外形图

单位: mm

-SE F1	尺寸		-E P	尺寸			
项目	Min.	Тур.	Max.	项目	Min.	Тур.	Max.
A			1.10	D	2.90	3.00	3.10
A1	0.05		0.15	Е	4.70	4.90	5.10
A2	0.75	0.85	0.95	E1	2.90	3.00	3.10
A3	0.30	0.35	0.40	e		0.65	
b	0.28		0.38	L	0.40		0.70
С	0.15		0.19	L1		0.95	

REEL SPECIFICATION

P/N	PKG	QTY
LMV358IDGKR-MS	TSSOP-8	2500



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